

GSMDD6911

60V P-Channel MOSFETs

Product Description

These P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

These devices are well suited for high efficiency fast switching applications.

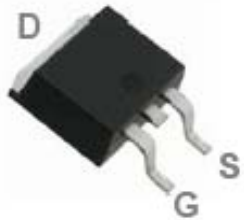
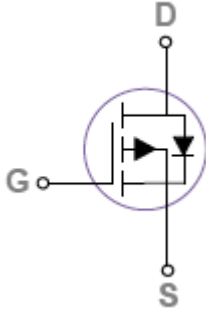
Features

- -60V, -7A, $R_{DS(ON)}=180m\Omega@V_{GS}=-10V$
- Improved dv/dt capability
- Fast switching
- 100% EAS guaranteed
- Green Device Available
- TO-252-2L package design

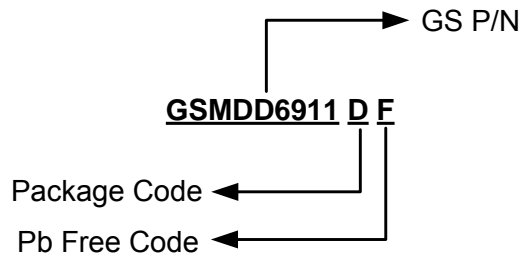
Applications

- Motor Drive
- Power Tools
- LED Lighting

Packages & Pin Assignments

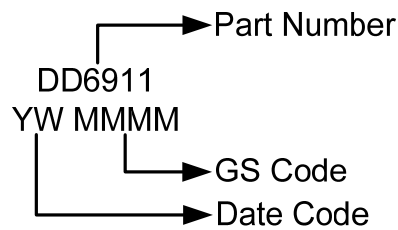
GSMDD6911DF (TO-252-2L)	
 <p>Top View</p>	
Description	
Gate	
Source	
Drain	

Ordering Information



Part Number	Package	Quantity Reel
GSMDD6911DF	TO-252-2L	2500 PCS

Marking Information



Absolute Maximum Ratings

T_A=25°C Unless otherwise noted

Symbol	Parameter	Typical	Unit
V _{DS}	Drain-Source Voltage	-60	V
V _{GS}	Gate –Source Voltage	±20	V
I _D	Continuous Drain Current	T _A =25°C	-7
		T _A =100°C	-4.4
I _{DM}	Pulsed Drain Current	-28	A
EAS	Single Pulse Avalanche Energy	32	mJ
IAS	Single Pulse Avalanche Current	-8	A
P _D	Power Dissipation (T _A =25°C)	15.6	W
	Power Dissipation (Derate above 25°C)	0.125	W/°C
T _J	Operating Junction Temperature Range	-50 to +150	°C
T _{STG}	Storage Temperature Range	-50 to +150	°C
R _{θJA}	Thermal Resistance-Junction to Ambient	62	°C/W
R _{θJC}	Thermal Resistance-Junction to Case	8	°C/W

Electrical Characteristics

T_A=25°C Unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-60			V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =-1mA		-0.05		V/°C
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250uA	-1.2	-1.6	-2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient			5		mV/°C
I _{GSS}	Gate Leakage Current	V _{DS} =0V, V _{GS} =±20V			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-60V, V _{GS} =0V			-1	uA
		V _{DS} =-48V, V _{GS} =0V, T _J =125°C			-10	
I _S	Continuous Source Current	V _G =V _D =0V, Force Current			-7	A
I _{SM}	Pulsed Source Current				-28	
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =-10V, I _D =-3A		153	180	mΩ
		V _{GS} =-4.5V, I _D =-1.5A		198	220	mΩ
g _{FS}	Forward Transconductance	V _{DS} =-10V, I _D =-2A		3		S
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =-1A			-1	V
Dynamic						
Q _g	Total Gate Charge	V _{DS} =-30V, V _{GS} =-10V, I _D =-3A		8.2	12	nC
Q _{gs}	Gate-Source Charge			1.8	3.6	
Q _{gd}	Gate-Drain Charge			1.5	3	
C _{iss}	Input Capacitance	V _{DS} =-30V, V _{GS} =0V, f=1MHz		425	615	pF
C _{oss}	Output Capacitance			35	50	
C _{rss}	Reverse Transfer Capacitance			20	30	
t _{d(on)}	Turn-On Time	V _{DD} =-30V, I _D =-1A, V _{GS} =-10V, R _G =6Ω		5.2	10	ns
t _r				19	36	
t _{d(off)}	Turn-Off Time			35	67	
t _f				10.6	20	

Typical Performance Characteristics

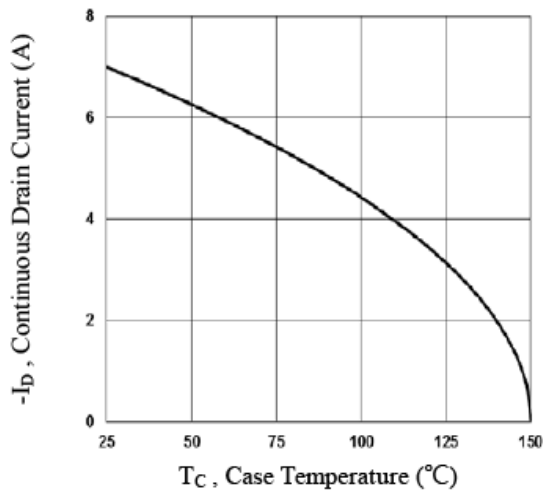


Fig.1 Continuous Drain Current vs. T_c

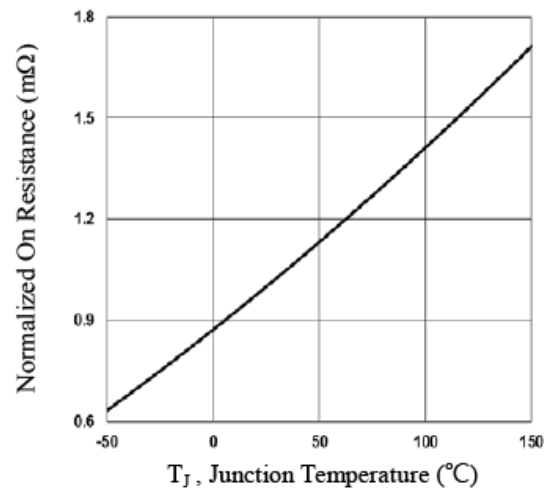


Fig.2 Normalized $R_{DS(on)}$ vs. T_j

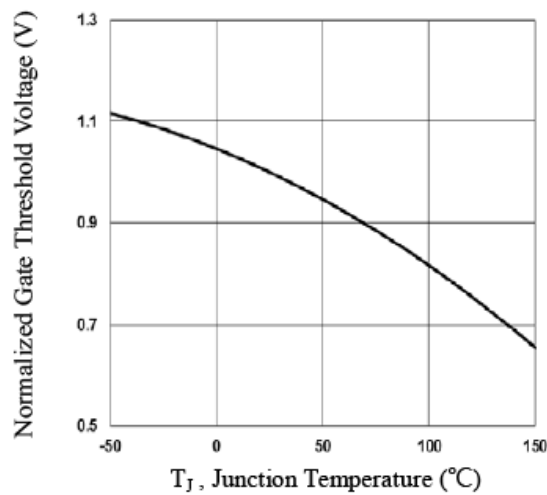


Fig.3 Normalized V_{th} vs. T_j

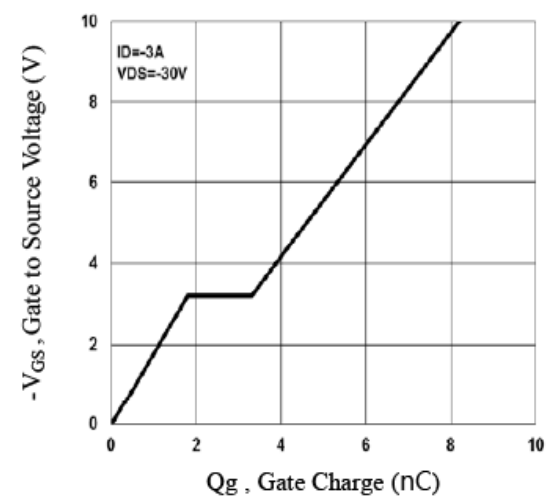


Fig.4 Gate Charge Waveform

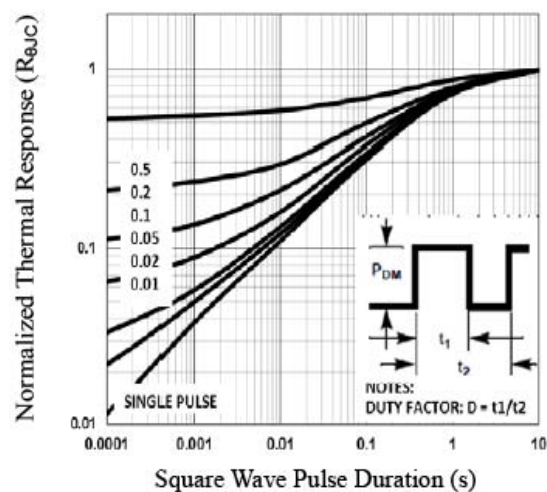


Fig.5 Normalized Transient Impedance

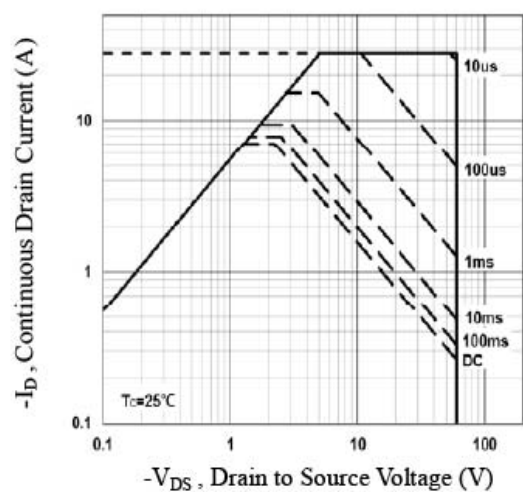
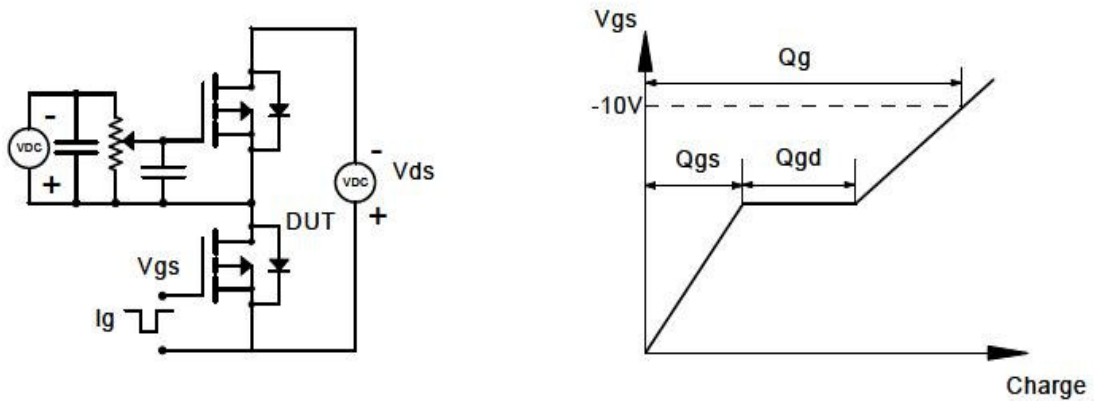


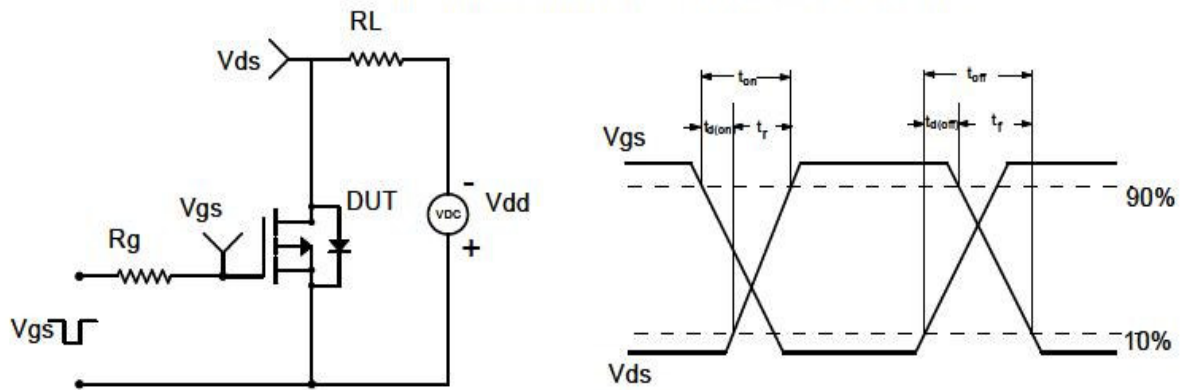
Fig.6 Maximum Safe Operation Area

Typical Performance Characteristics (Continue)

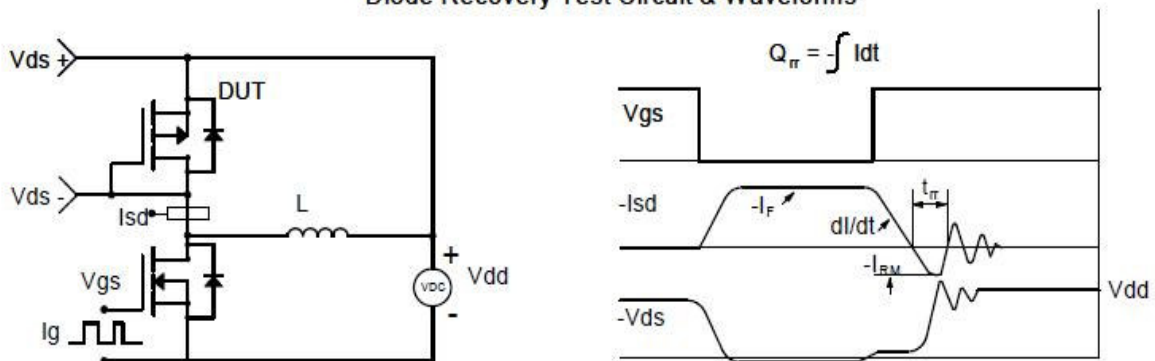
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

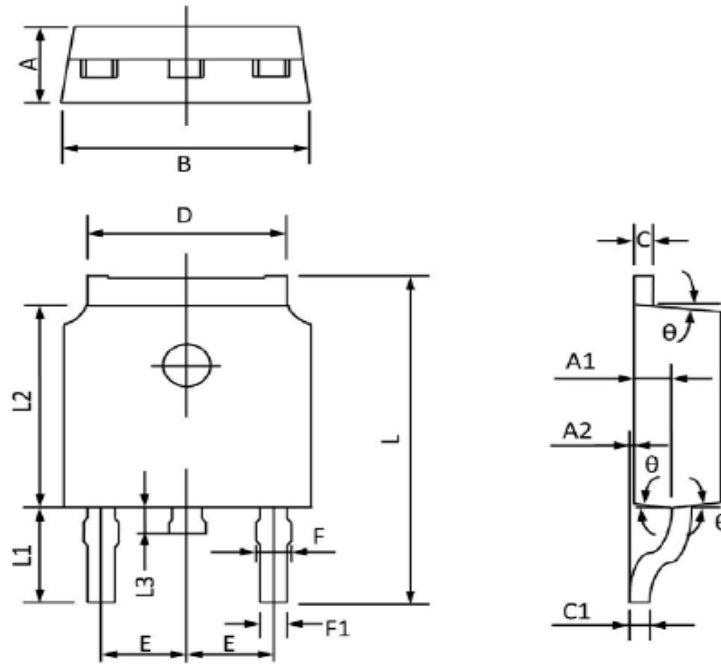


Diode Recovery Test Circuit & Waveforms



Package Dimension

TO-252-2L



Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	2.20	2.40	0.087	0.094
A1	0.91	1.11	0.036	0.044
A2	0.00	0.15	0.000	0.006
B	6.50	6.70	0.256	0.264
C	0.46	0.58	0.018	0.030
C1	0.46	0.58	0.018	0.030
D	5.10	5.46	0.201	0.215
E	2.186	2.386	0.086	0.094
F	0.74	0.94	0.029	0.037
F1	0.66	0.86	0.026	0.034
L	9.80	10.40	0.386	0.409
L1	2.9 (REF)		0.114 (REF)	
L2	6.00	6.20	0.236	0.244
L3	0.60	1.00	0.024	0.039
θ	3°	9°	3°	9°

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